

# QN7002

# N-CHANNEL MOSFET FOR SWITCHING

## Description

The QN7002, N-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.5 V power source.

## Features

• Directly driven by a 4.5 V power source.

• Low on-state resistance

 $R_{DS(on)1} = 2.7 \ \Omega \ MAX. \ (V_{GS} = 10 \ V, \ I_D = 100 \ mA) \\ R_{DS(on)2} = 3.2 \ \Omega \ MAX. \ (V_{GS} = 4.5 \ V, \ I_D = 50 \ mA)$ 

## **Ordering Information**

| Part Number   | Lead Plating | Packing    | Package           |
|---------------|--------------|------------|-------------------|
| QN7002-T1B-AT | Pure Sn      | 3000p/Reel | SC-59 (Mini Mold) |

**Remark** "-AT" indicates Pb-free. This product does not contain Pb in external electrode and other parts.

## **Remark for Agent**

ORDER NUMBER "2SK4079(1)" must be used to order, instead of "QN7002". For instance, "2SK4079(1)-T1B-AT"

## Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

| Drain to Source Voltage (V <sub>GS</sub> = 0 V) | VDSS     | 60          | V  |
|---|----------|-------------|----|
| Gate to Source Voltage ( $V_{DS}$ = 0 V)        | Vgss     | ±20         | V  |
| Drain Current (DC)                              | D(DC)    | 200         | mA |
| Drain Current (pulse) <sup>Note</sup>           | D(pulse) | ±800        | mA |
| Total Power Dissipation                         | Ρτ       | 200         | mW |
| Channel Temperature                             | Tch      | 150         | °C |
| Storage Temperature                             | Tstg     | -55 to +150 | °C |
|   |          |             |    |

**Note** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

VESD ±400 V (MIL STD; C = 100 pF, R = 1.5 k $\Omega$ , 5 times), as reference value.

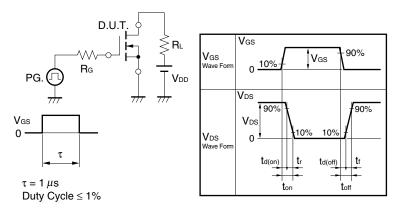


# Electrical Characteristics (T<sub>A</sub> = 25°C)

| Characteristics                                     | Symbol              | Test Conditions   | MIN. | TYP. | MAX. | UNIT |
|---|---------------------|---|------|------|------|------|
| Zero Gate Voltage Drain Current                     | IDSS                | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V                           |      |      | 1    | μA   |
| Gate Leakage Current                                | lgss                | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                       |      |      | ±10  | μA   |
| Gate Threshold Voltage                              | $V_{\text{GS(th)}}$ | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$                                    | 1.0  |      | 2.5  | V    |
| Forward Transfer Admittance Note                    | y <sub>fs</sub>     | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 100 mA                         | 150  |      |      | mS   |
| Drain to Source On-state Resistance <sup>Note</sup> | RDS(on)1            | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA                         |      | 2.1  | 2.7  | Ω    |
|   | RDS(on)2            | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 mA                         |      | 2.4  | 3.2  | Ω    |
| Input Capacitance                                   | Ciss                | V <sub>DS</sub> = 10 V,   |      | 20   |      | pF   |
| Output Capacitance                                  | Coss                | V <sub>GS</sub> = 0 V,  |      | 9    |      | pF   |
| Reverse Transfer Capacitance                        | Crss                | f = 1.0 MHz   |      | 2    |      | pF   |
| Turn-on Delay Time                                  | td(on)              | V <sub>DD</sub> = 10 V,   |      | 16   |      | ns   |
| Rise Time   | tr                  | I⊳ = 200 mA,  |      | 6.5  |      | ns   |
| Turn-off Delay Time                                 | td(off)             | V <sub>GS</sub> = 10 V,   |      | 82   |      | ns   |
| Fall Time   | tr                  | R <sub>G</sub> = 10 Ω   |      | 32   |      | ns   |
| Total Gate Charge                                   | QG                  | I <sub>D</sub> = 200 mA, V <sub>DD</sub> = 25 V, V <sub>GS</sub> = 10 V |      | 2    |      | nC   |
| Body Diode Forward Voltage                          | VF(S-D)             | IF = 200 mA, VGS = 0 V  |      | 0.86 |      | V    |

Note Pulsed

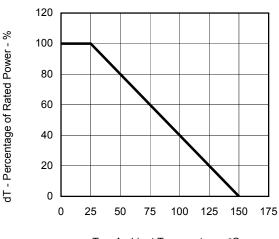
# **Test Circuit Switching Time**





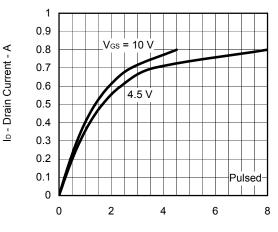
# Typical Characteristics (T<sub>A</sub> = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

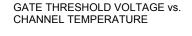


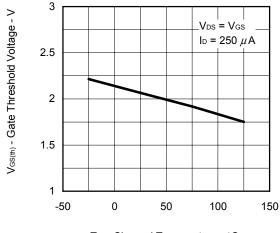
 $T_A-Ambient$  Temperature -  $^\circ C$ 





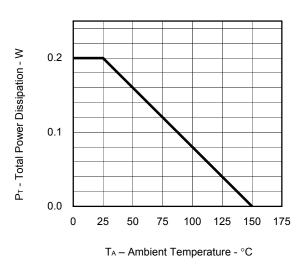
V<sub>DS</sub> - Drain to Source Voltage - V



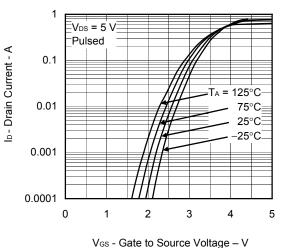


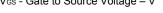
T<sub>ch</sub> - Channel Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

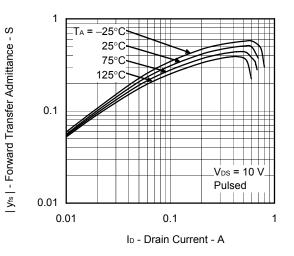


#### FORWARD TRANSFER CHARACTERISTICS

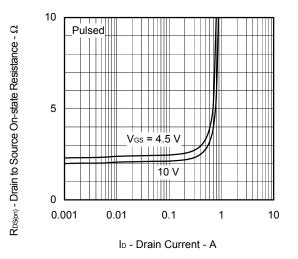




FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

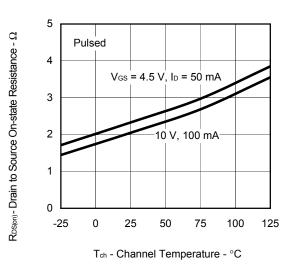




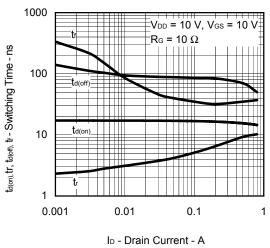


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

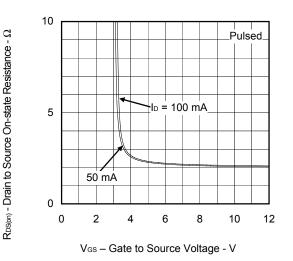
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



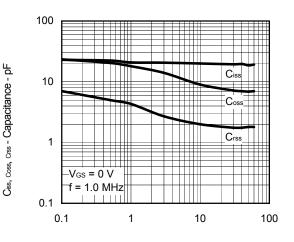


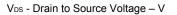


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

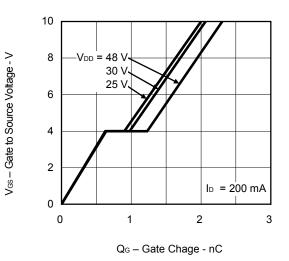


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



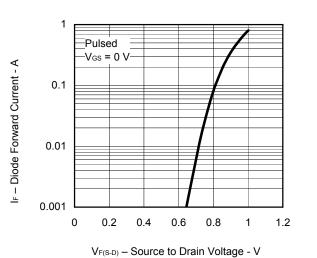


#### DYNAMIC INPUT CHARACTERISTICS



R07DS0269EJ0100 Rev.1.00

Mar 11, 2011

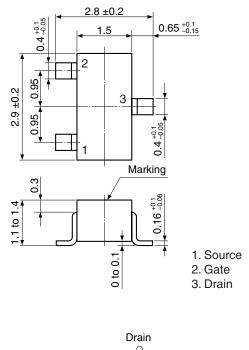


### SOURCE TO DRAIN DIODE FORWARD VOLTAGE

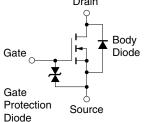


# Package Drawings (Unit: mm)

## SC-59 (Mini Mold)



# **Equivalent Circuit**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.



| <b>Revision History</b> | QN7002 Data Sheet |
|-------------------------|-------------------|
| <b>Revision History</b> | QN700             |

|      |              | Description |                      |  |
|------|--------------|-------------|----------------------|--|
| Rev. | Date         | Page        | Summary              |  |
| 1.00 | Mar 11, 2011 | -           | First Edition Issued |  |

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